

2SC6012

Silicon NPN triple diffusion mesa type

For horizontal deflection output

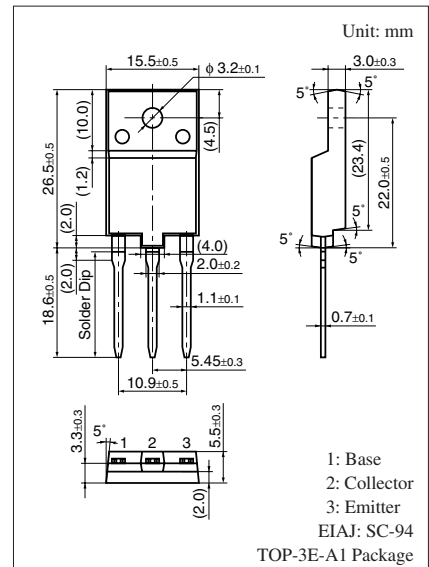
■ Features

- High breakdown voltage, and high reliability through the use of a glass passivation layer
- High-speed switching
- Wide safe operation area

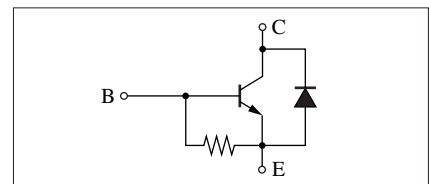
■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	1 700	V
Collector-emitter voltage (E-B short)	V_{CES}	1 700	V
Emitter-base voltage (Collector open)	V_{EBO}	7	V
Base current	I_B	3	A
Collector current	I_C	15	A
Peak collector current *	I_{CP}	24	A
Collector power dissipation	P_C	60	W
	$T_a = 25^\circ\text{C}$	3	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: Non-repetitive peak collector current



Internal Connection

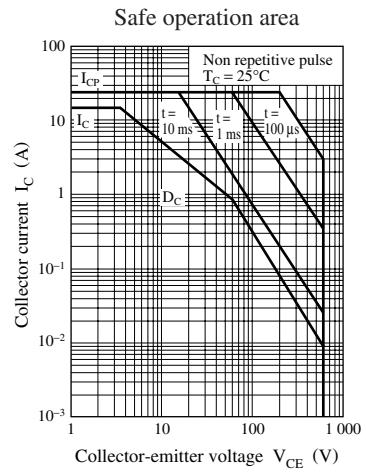
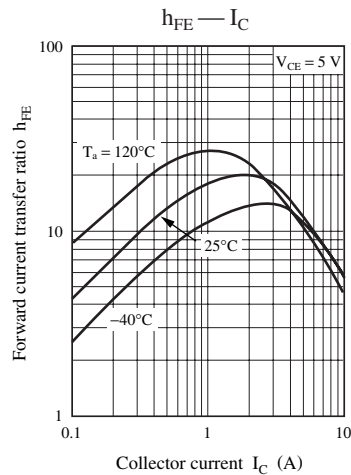
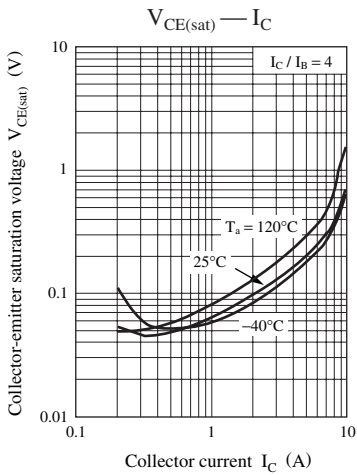
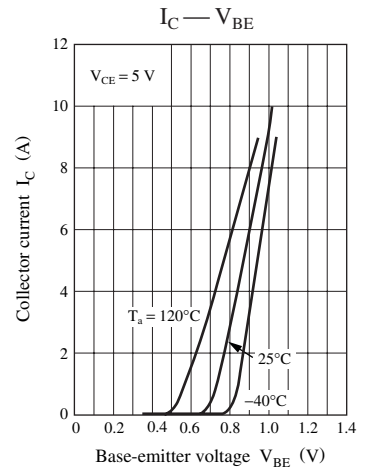
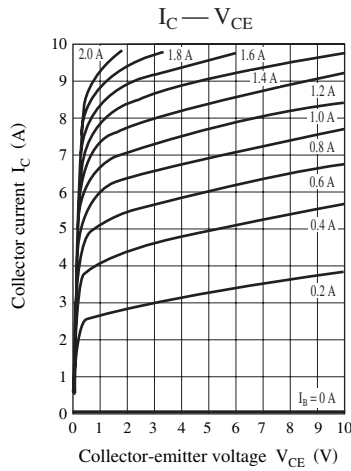
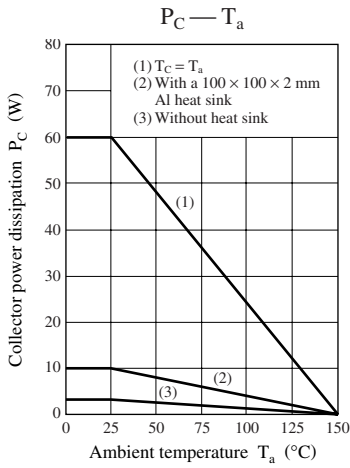


■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

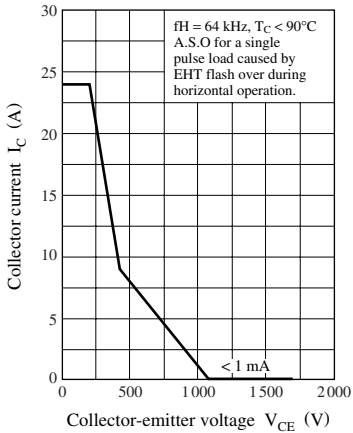
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Emitter-base voltage (Collector open) *	V_{EBO}	$I_E = 750 \text{ mA}, I_C = 0$	7			V
Forward voltage *	V_F	$I_F = 7.0 \text{ A}$			-2	V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 1 000 \text{ V}, I_E = 0$			50	μA
		$V_{CB} = 1 700 \text{ V}, I_E = 0$			1	mA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 5 \text{ V}, I_C = 7.0 \text{ A}$	7		12	—
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = 7.0 \text{ A}, I_B = 1.75 \text{ A}$			3.0	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = 7.0 \text{ A}, I_B = 1.75 \text{ A}$			1.5	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_C = 0.5 \text{ A}, f = 0.5 \text{ MHz}$		2.1		MHz
Storage time	t_{stg}	$I_C = 7.0 \text{ A}, \text{Resistance loaded}$			5.0	μs
Fall time	t_f	$I_{B1} = 1.75 \text{ A}, I_{B2} = -3.5 \text{ A}$			0.5	μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Pulse measurement



Safe operation area (Horizontal operation)



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